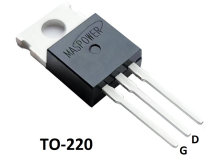
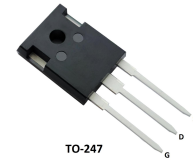
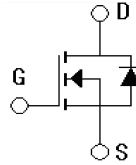


## Features

- Very low FOM  $R_{DS(on)} \times Q_g$
- 100% avalanche tested
- Easy to use/drive
- RoHS compliant

## Applications

- Switch Mode Power Supply (SMPS)
- Uninterruptible Power Supply (UPS)
- Power Factor Correction (PFC)
- Low Power Chargers and Adapters



## Absolute Ratings (Tc=25°C)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DSS}$	850	V
Drain Current-continuous	$I_D$ T=25°C	20	A
	T=100°C	10	A
Drain Current-pulse (note 1)	$I_{DM}$	80	A
Gate-Source Voltage	$V_{GSS}$	±30	V
Single Pulsed Avalanche Energy (note 2)	$E_{AS}$	1125	mJ
Repetitive Avalanche Energy(note 2)	$E_{AR}$	27.8	mJ
Avalanche Current	$I_{AR}$	4.6	A
MOSFET dv/dt Ruggedness, VDS = 0...480V	dv/dt	50	V/ns
Continuous Diode Forward Current	$I_S$	20	A
Diode Pulsed Current(note 1)	$I_{S,pulse}$	69	A
Reverse Diode dv/dt(note 3)	dv/dt	15	V/ns
Maximum Diode Commutation Speed(note 3)	di/dt	500	A/μs
Power Dissipation (TO-247/TO-220)	PD	183	W
Power Dissipation (TO-220F)	PD	68	W
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55~+150	°C

## Electrical Characteristics( $T_{CASE}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Tests conditions	Min	Typ	Max	Units
Drain-Source Voltage	$BV_{DSS}$	$I_D=250\mu A, V_{GS}=0V$	850	-	-	V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=800V, V_{GS}=0V, T_C=25^{\circ}C$	-	-	1	$\mu A$
		$V_{DS}=800V, T_C=150^{\circ}C$	-	-	100	$\mu A$
Gate body leakage current	$I_{GSS}$	$V_{DS}=0V, V_{GS}=\pm 30V$	-	-	$\pm 100$	nA
<b>On-Characteristics</b>						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	2.5	-	4.5	V
Static Drain-Source On-Resistance	$R_{DS(ON)}$	$V_{GS}=10V, I_D=10A$	-	320	380	m $\Omega$
Gate Resistance	$R_G$	f = 1.0MHz open drain	-	1.5	-	$\Omega$
<b>Dynamic Characteristics</b>						
Input capacitance	$C_{iss}$	$V_{DS}=100V, V_{GS}=0V, f=1.0MHZ$	-	2468.4	-	pF
Output capacitance	$C_{oss}$		-	56.81	-	pF
Reverse transfer capacitance	$C_{rss}$		-	5.2	-	pF

## Electrical Characteristics( $T_{CASE}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Tests conditions	Min	Typ	Max	Units
<b>Switching-Characteristics</b>						
Turn-On delay time	$t_{d(on)}$	$V_{DD}=400V, I_D=20A, R_G=25\Omega$	-	68.45	-	ns
Turn-On rise time	$t_r$		-	76.9	-	ns
Turn-Off delay time	$t_{d(Off)}$		-	180.2	-	ns
Turn-Off rise time	$t_f$		-	58.35	-	ns
Total Gate Charge	$Q_g$	$V_{DS}=640V, I_D=20A, V_{GS}=10V$	-	54.9	-	nC
Gate-Source charge	$Q_{gs}$		-	10.4	-	nC
Gate-Drain charge	$Q_{gd}$		-	21.5	-	nC
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						

Source-Drain Current (Body Diode)	$I_{SD}$	$T_C=25^\circ\text{C}$	-	-	10	A
Reverse recovery time	$t_{rr}$	$V_R=400, I_F=20\text{A}$ $di_F/dt=100\text{A}/\mu\text{s}$	-	405.4	-	ns
Reverse recovery charge	$Q_{rr}$		-	4.633	-	$\mu\text{C}$
Peak Reverse Recovery Current	$I_{rrm}$		-	22.83	-	A

## Thermal Characteristic

Parameter	Symbol	Value		Unit
		TO-247/ TO-220	TO-220F	
Thermal Resistance, junction to Case	$R_{th(j-C)}$	0.68	1.84	$^\circ\text{C}/\text{W}$
Thermal Resistance, junction to Ambient	$R_{th(j-A)}$	62.5	62.5	$^\circ\text{C}/\text{W}$

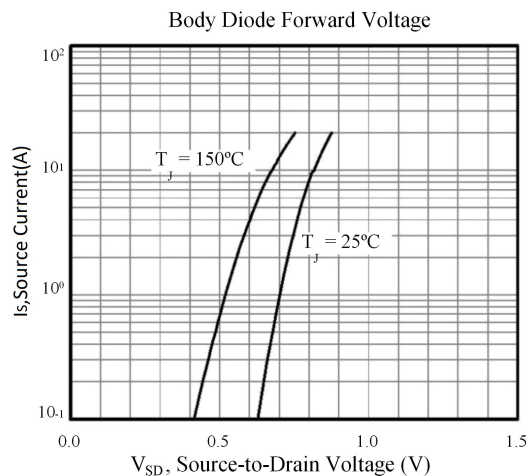
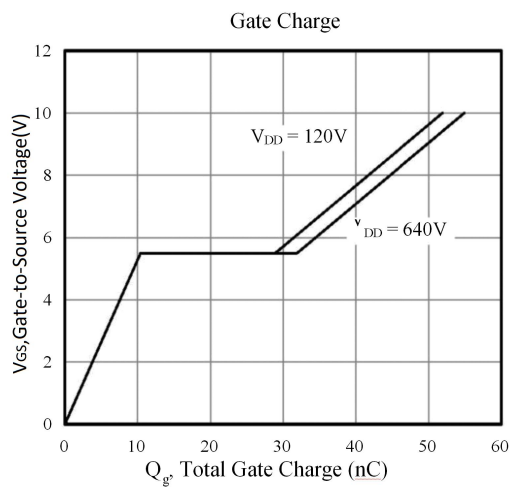
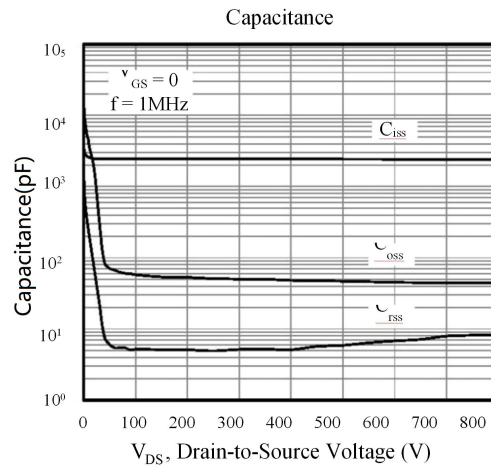
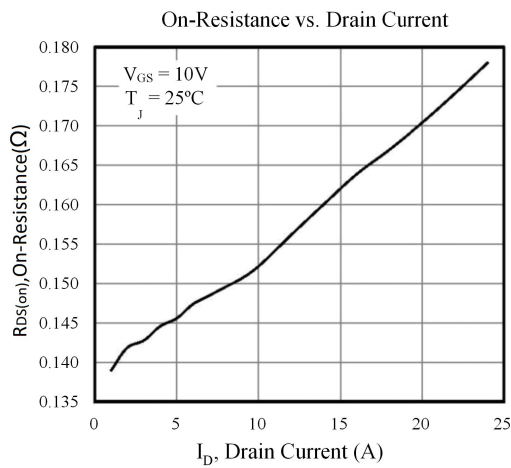
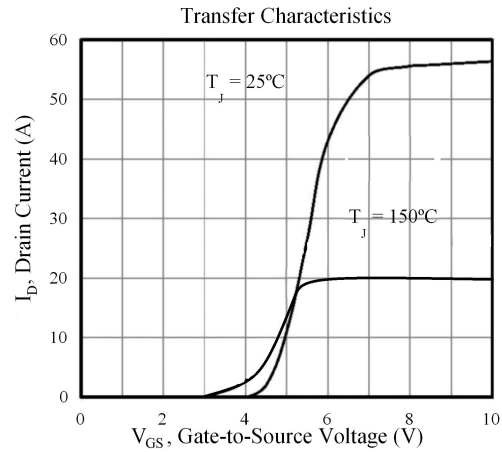
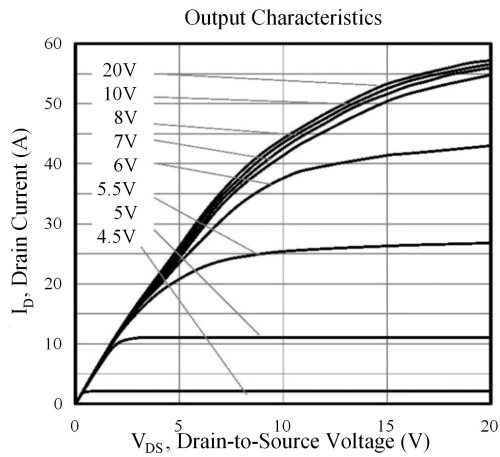
Notes:

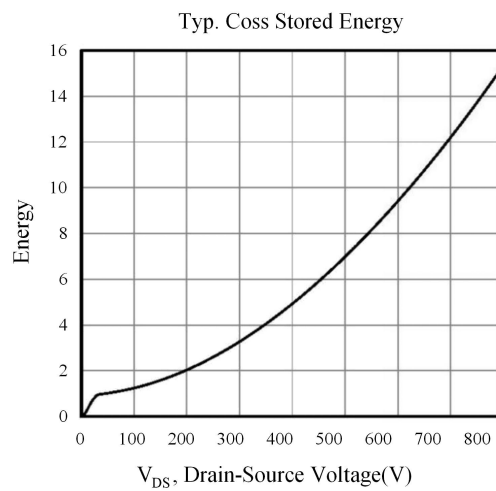
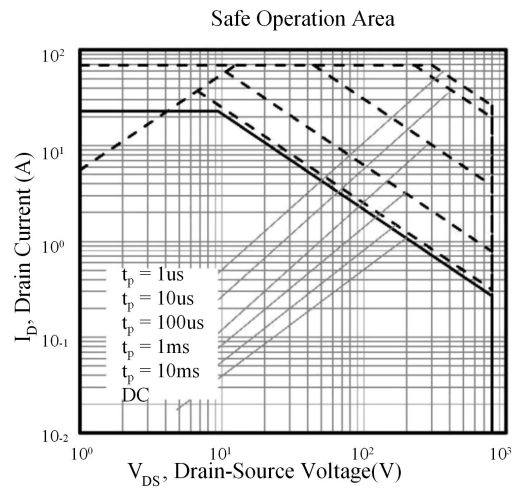
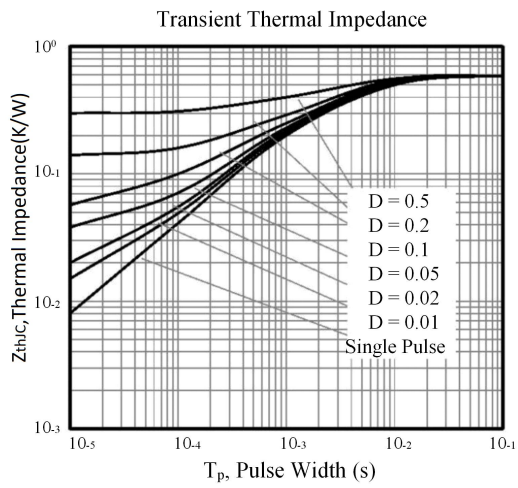
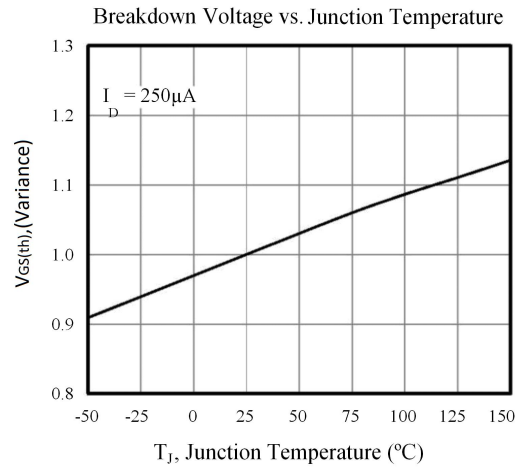
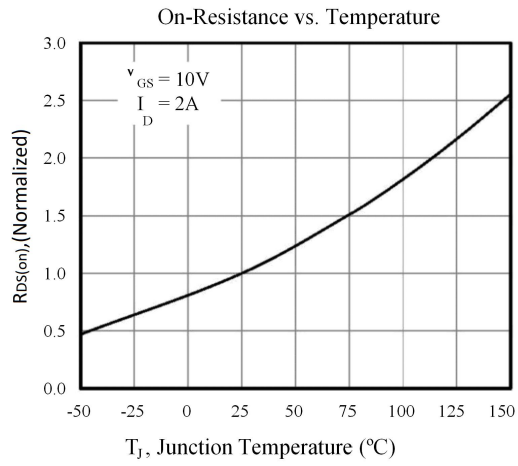
1. Repetitive Rating: Pulse width limited by maximum junction temperature
2.  $I_D = 10\text{A}$ ,  $V_{DD} = 50\text{V}$ ,  $R_G = 25\Omega$ , Starting  $T_J = 25^\circ\text{C}$
3. Identical low side and high side switch with identical  $R_G$

## Order information

Order codes	Package	Packaging
MS20N85ICC0	TO-247	Tube
MS20N85ICT0	TO-220	Tube
MS20N85ICT1	TO-220F	Tube

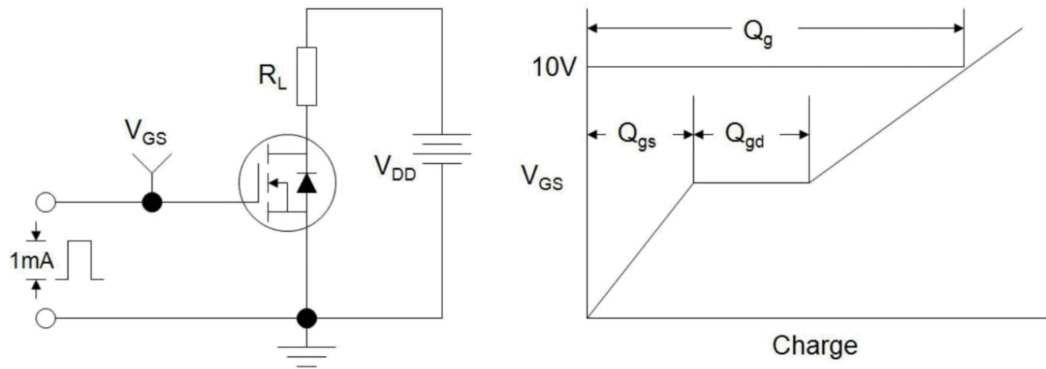
## Typical Characteristics (T<sub>J</sub> = 25° C, unless otherwise noted)



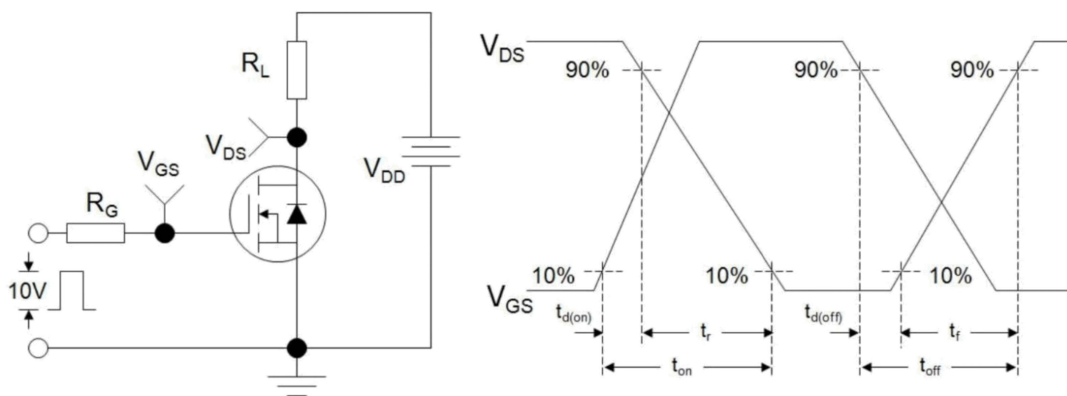


### Test Circuit

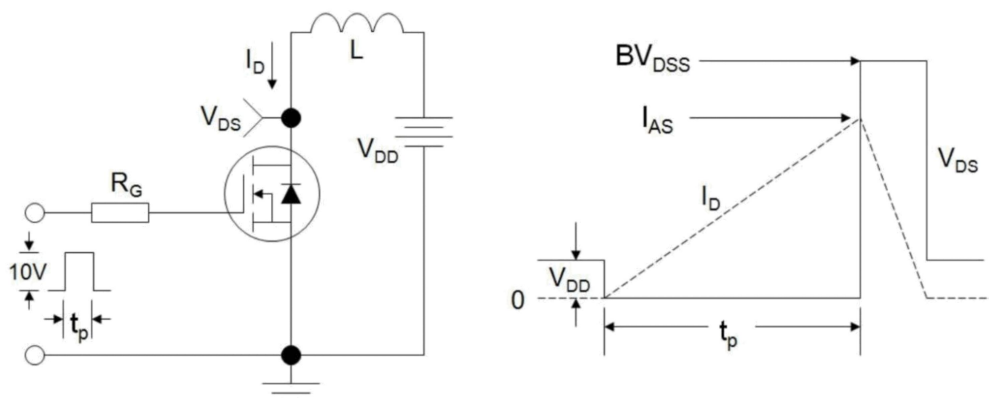
Gate Charge Test Circuit and Waveform



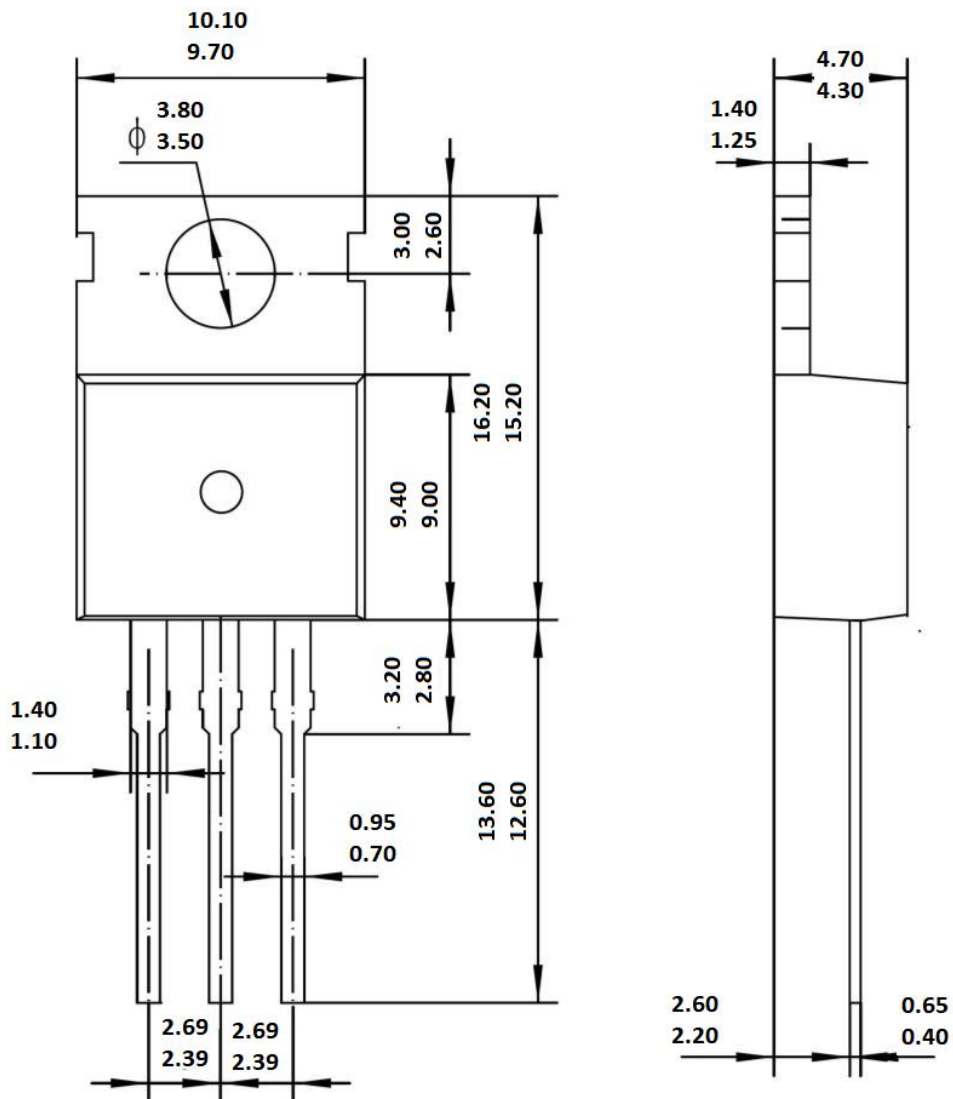
Resistive Switching Test Circuit and Waveform



Unclamped Inductive Switching Test Circuit and Waveform



### Package Mechanical DATA



**TO-220**

**Unit: mm**

